

claim 10
a first passivation layer formed on said adhesion layer, said first passivation layer and said adhesion layer including at least one common chemical element.

b6
19. (Amended) The integrated circuit of claim 17 wherein said oxide layer includes silicon dioxide (SiO_2).

b7
23. (Amended) An integrated circuit comprising in a three layer stack:
a silicon dioxide insulating layer;
a silicon oxynitride adhesion layer formed on said silicon dioxide insulating layer;
and
a silicon nitride hard passivation layer formed on said silicon oxynitride adhesion layer.
